NDT02N60Z

N-Channel Power MOSFET 600 V, 8.0 Ω

Features

- 100% Avalanche Tested
- Extremely High dv/dt Capability
- Gate Charge Minimized
- Zener−protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

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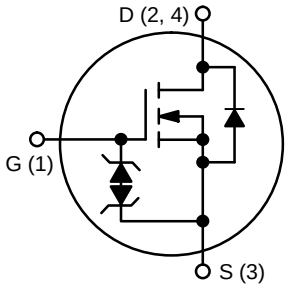
http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX
600 V	8.0 Ω @ 10 V

N−Channel



ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	600	V
Gate−to−Source Voltage	V_{GS}	±30	V
Continuous Drain Current $R_{\theta JA}$ Steady State, T_C = 25°C	I_D	0.3	A
Continuous Drain Current $R_{\theta JA}$ Steady State, T_C = 100°C	I_D	0.21	A
Power Dissipation – $R_{\theta JA}$ Steady State, T_C = 25°C	P_D	2.0	W
Pulsed Drain Current	I_{DM}	5	A
Continuous Source Current (Body Diode)	I_S	2.2	A
Single Pulse Drain−to−Source Avalanche Energy (I_D = 1.4 A)	EAS	38	mJ
Peak Diode Recovery (Note 1)	dV/dt	4.5	V/ns
Maximum Temperature for Soldering Leads	T_L	260	°C
Operating Junction and Storage Temperature	T_J, T_{STG}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_S < 2.2 A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, T_J = +150°C

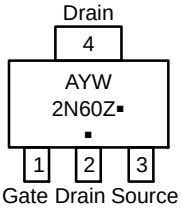
THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction−to−Ambient Steady State NDT02N60Z (Note 2) NDT02N60Z (Note 3)	$R_{\theta JA}$	 61 148	°C/W

2. Surface mounted on FR4 board using 1″ sq. pad size (Cu area = 1.127″ sq. [2 oz] including traces)
3. Surface−mounted on FR4 board using minimum recommended pad size (Cu area = 0.026” sq. [2 oz]).

MARKING DIAGRAM

SOT−223
CASE 318E
STYLE 3



A = Assembly Location
Y = Year
W = Work Week
2N60Z = Specific Device Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA		600			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	Reference to 25°C, I_D = 1 mA			605		mV/°C
Drain−to−Source Leakage Current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	T_J = 25°C			1	μA
			T_J = 125°C			50	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = ±20 V				±10	μA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 50 μA		3.0	3.9	4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	Reference to 25°C, I_D = 50 μA			10.2		mV/°C
Static Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.7 A			5.9	8.0	Ω
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 0.7 A			1.3		S
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 5)	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz			170		pF
Output Capacitance (Note 5)	C_{oss}				22		
Reverse Transfer Capacitance (Note 5)	C_{rss}				4.8		
Effective output capacitance, energy related (Note 7)	$C_{o(er)}$	V_{GS} = 0 V, V_{DS} = 0 to 480 V			7.8		
Effective output capacitance, time related (Note 8)	$C_{o(tr)}$	I_D = constant, V_{GS} = 0 V, V_{DS} = 0 to 480 V			12.4		
Total Gate Charge (Note 5)	Q_g	V_{DS} = 300 V, I_D = 1.6 A, V_{GS} = 10 V			7.4		nC
Gate-to-Source Charge (Note 5)	Q_{gs}				1.8		
Gate-to-Drain (“Miller”) Charge (Note 5)	Q_{gd}				3.8		
Plateau Voltage	V_{GP}				6.4		V
Gate Resistance	R_g				11.5		Ω
RESISTIVE SWITCHING CHARACTERISTICS (Note 6)							
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 300 V, I_D = 1.6 A, V_{GS} = 10 V, R_G = 0 Ω			10		ns
Rise Time	t_r				6		
Turn-off Delay Time	$t_{d(off)}$				14		
Fall Time	t_f				8		
SOURCE−DRAIN DIODE CHARACTERISTICS							
Diode Forward Voltage	V_{SD}	I_S = 1.6 A, V_{GS} = 0 V	T_J = 25°C		0.9	1.2	V
			T_J = 100°C		0.8		
Reverse Recovery Time	t_{rr}	V_{GS} = 0 V, V_{DD} = 30 V, I_S = 1.6 A, d_i/d_t = 100 A/μs			230		ns
Charge Time	t_a				50		
Discharge Time	t_b				180		
Reverse Recovery Charge	Q_{rr}				495		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.
5. Guaranteed by design.
6. Switching characteristics are independent of operating junction temperatures.
7. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$
8. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

TYPICAL CHARACTERISTICS

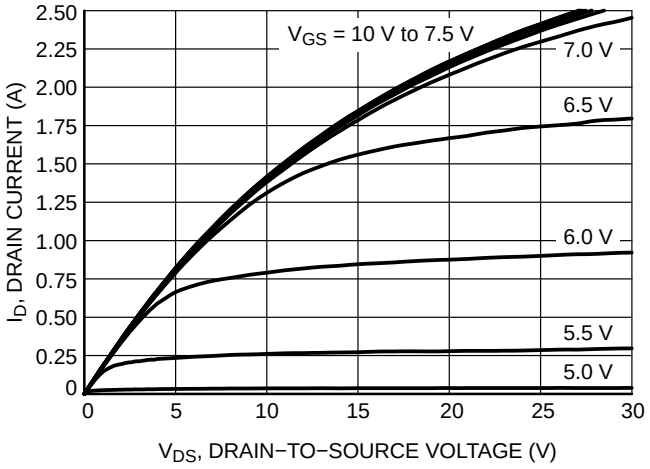


Figure 1. On−Region Characteristics

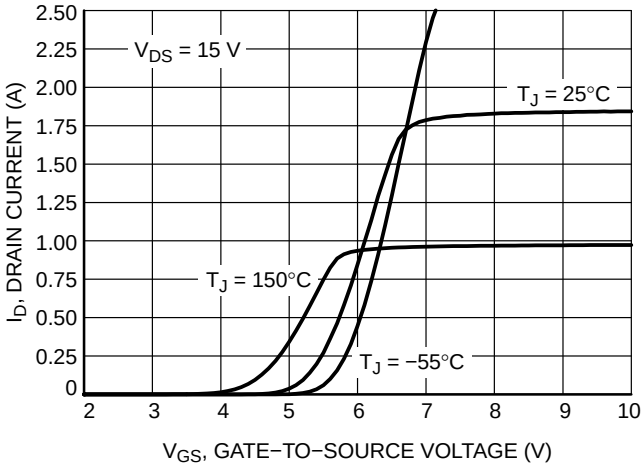


Figure 2. Transfer Characteristics

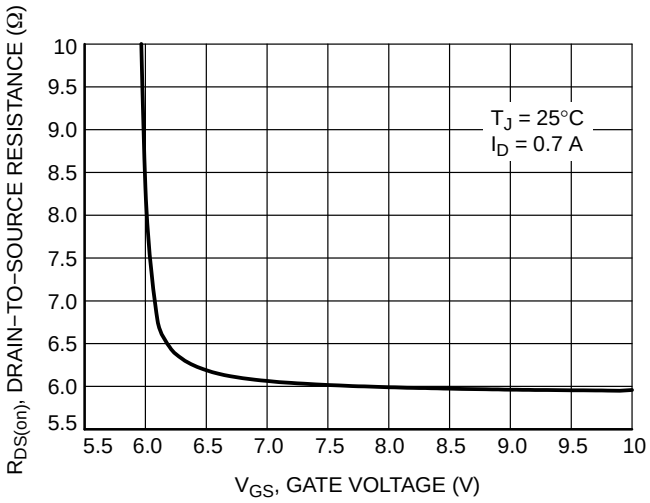


Figure 3. On−Resistance vs. Gate−to−Source Voltage

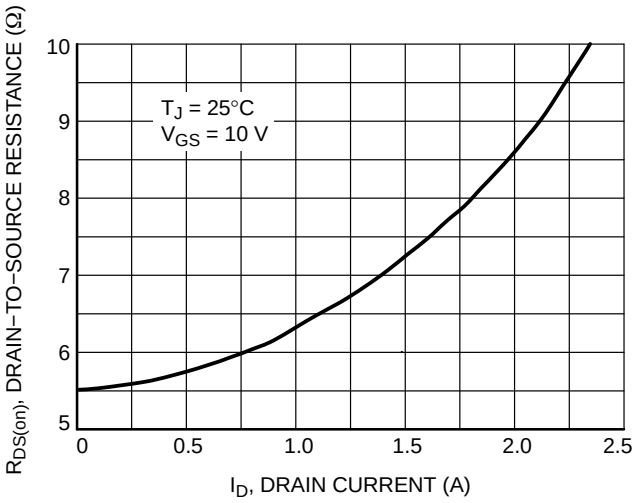


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

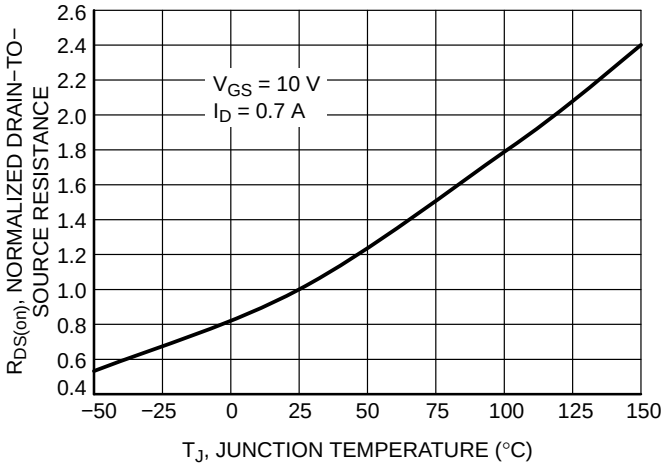


Figure 5. On−Resistance Variation with Temperature

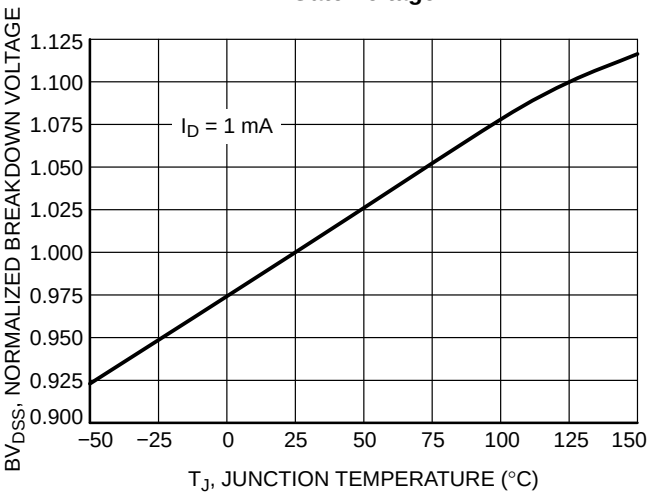


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

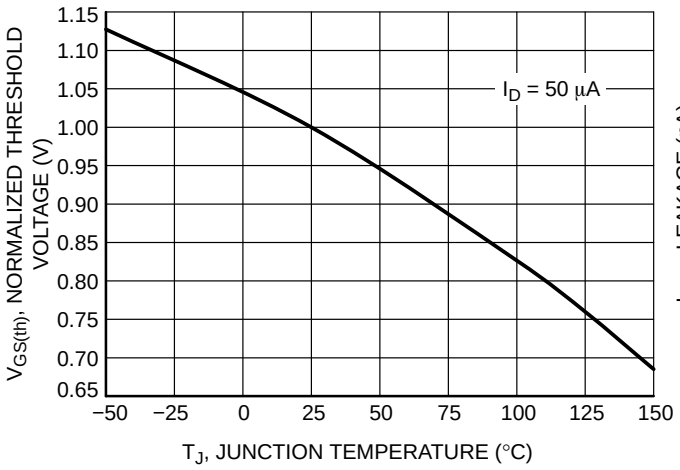


Figure 7. Threshold Voltage Variation with Temperature

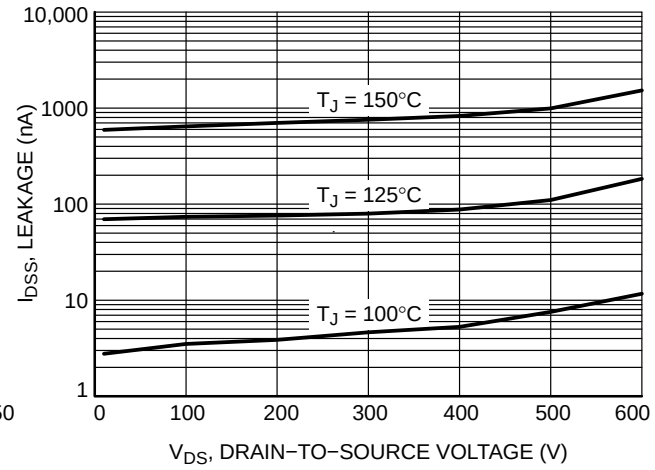


Figure 8. Drain−to−Source Leakage Current vs. Voltage

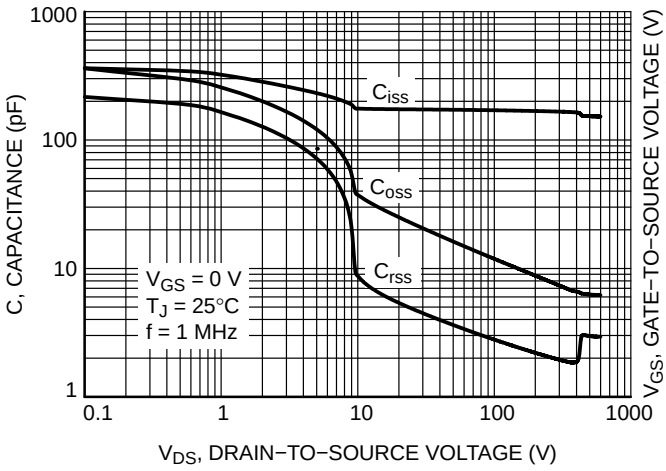


Figure 9. Capacitance Variation

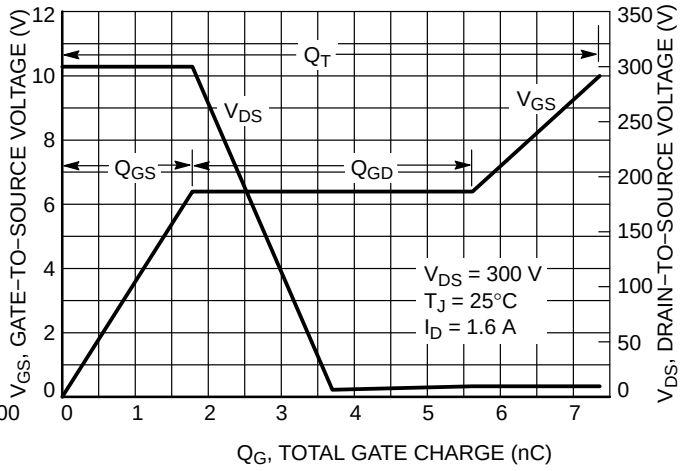


Figure 10. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

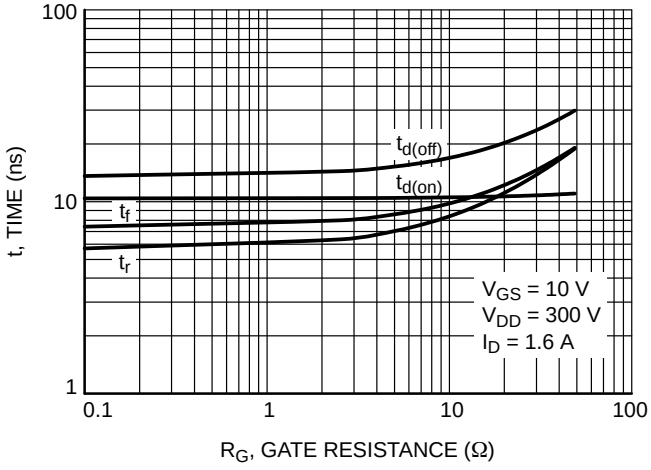


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

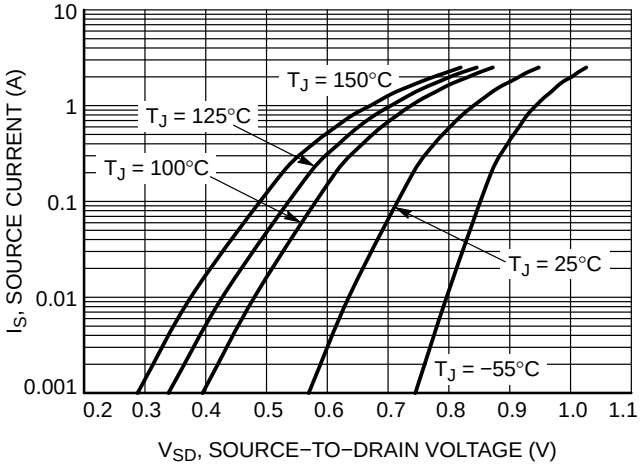


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

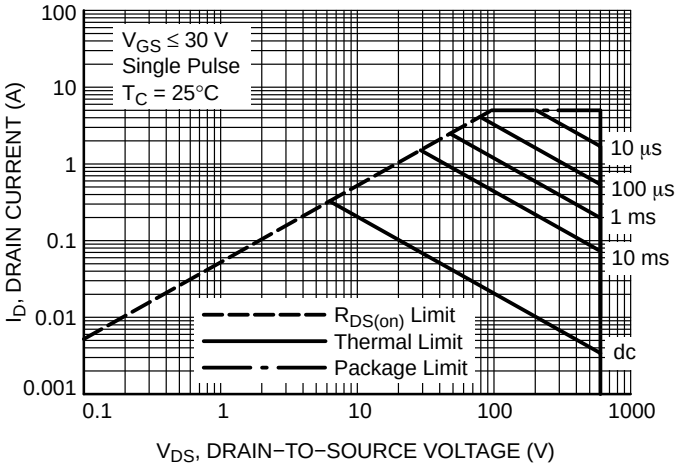


Figure 13. Maximum Rated Forward Biased Safe Operating Area

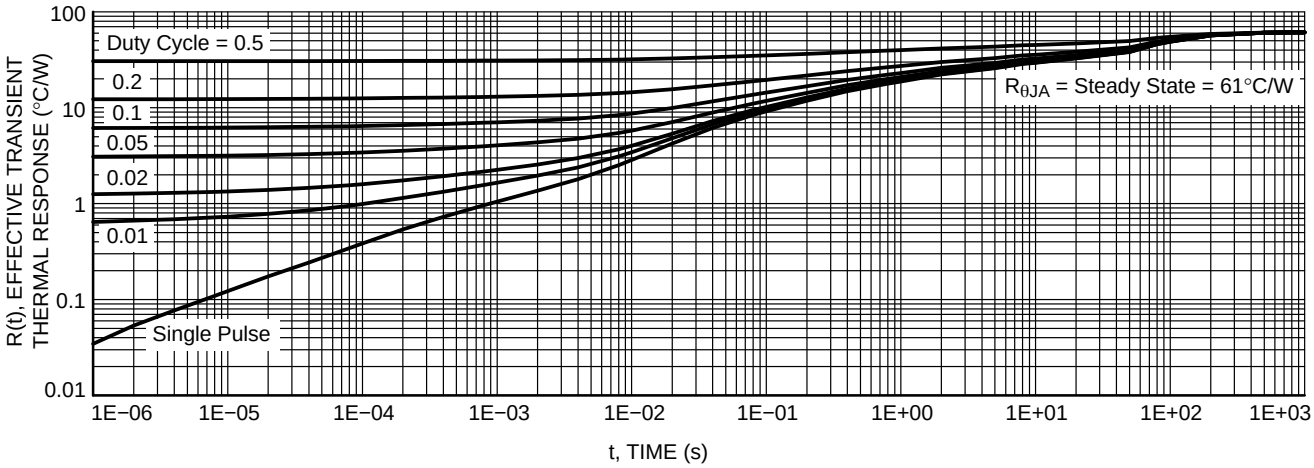


Figure 14. Thermal Impedance (Junction−to−Ambient)

ORDERING INFORMATION

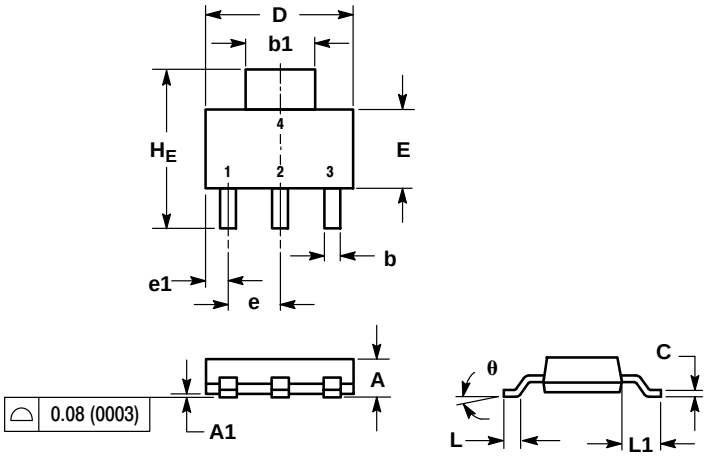
Device	Package	Shipping†
NDT02N60ZT1G	SOT−223 (Pb−Free, Halogen Free)	1000 / Tape & Reel
NDT02N60ZT3G		4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NDT02N60Z

PACKAGE DIMENSIONS

SOT−223 (TO−261)
CASE 318E−04
ISSUE N

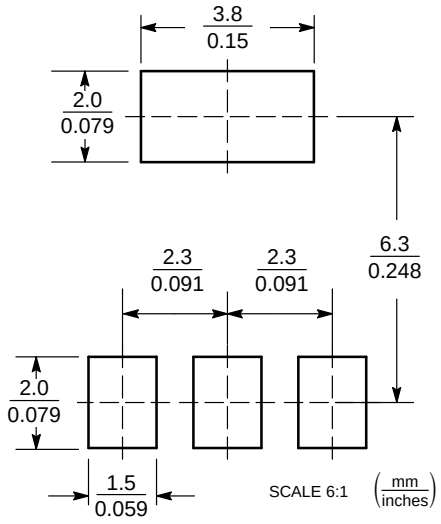


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	−−−	−−−	0.008	−−−	−−−
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	–	10°	0°	–	10°

STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT



PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

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